

NPN SILICON RF POWER TRANSISTOR

DESCRIPTION:

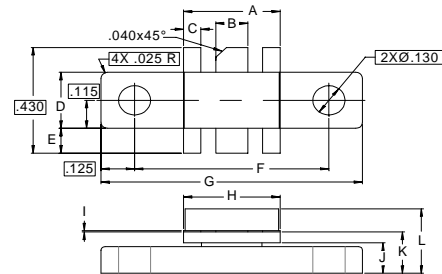
The **ASI UHBS30-1** is Designed for Class C, FM Base Applications up to 900 MHz.

FEATURES:

- Internal Input Matching Network
- $P_G = 7.5$ dB at 30 W/900 MHz
- **Omnigold™** Metalization System

MAXIMUM RATINGS

I_C	9.0 A
V_{CBO}	50 V
V_{CEO}	30 V
V_{EBO}	4.0 V
P_{DISS}	100 W @ $T_C = 25^\circ\text{C}$
T_J	-65 °C to +200 °C
T_{STG}	-65 °C to +150 °C
θ_{JC}	1.5°C/W

PACKAGE STYLE .230 6L FLG


DIM	MINIMUM inches / mm	MAXIMUM inches / mm
A	.355 / 9.02	.365 / 9.27
B	.115 / 2.92	.125 / 3.18
C	.075 / 1.91	.085 / 2.16
D	.225 / 5.72	.235 / 5.97
E	.090 / 2.29	.110 / 2.79
F	.720 / 18.29	.730 / 18.54
G	.970 / 24.64	.980 / 24.89
H	.355 / 9.02	.365 / 9.27
I	.004 / 0.10	.006 / 0.15
J	.120 / 3.05	.130 / 3.30
K	.160 / 4.06	.180 / 4.57
L	.230 / 5.84	.260 / 6.60

ORDER CODE: ASI10670
CHARACTERISTICS $T_C = 25^\circ\text{C}$

SYMBOL	TEST CONDITIONS	MINIMUM	TYPICAL	MAXIMUM	UNITS
BV_{CEO}	$I_C = 50$ mA	30			V
BV_{CES}	$I_C = 50$ mA $R_{BE} = 10 \Omega$	50			V
BV_{EBO}	$I_E = 10$ mA	4.0			V
I_{CBO}	$V_{CE} = 15$ V			5	mA
I_{CES}	$V_{CE} = 24$ V			10	mA
h_{FE}	$V_{CE} = 5.0$ V $I_C = 1.0$ A	10		---	---
C_{ob}	$V_{CB} = 25$ V $f = 1.0$ MHz			50	pF
P_G	$V_{CE} = 24$ V $P_{OUT} = 30$ W $f = 900$ GHz	7.5			dB
η_c			55		%